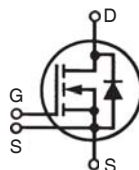


X-Class HiPerFET™ Power MOSFET

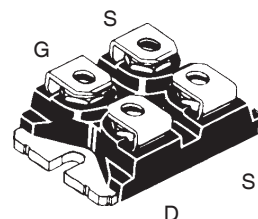
IXFN70N100X

N-Channel Enhancement Mode
Avalanche Rated



$$\begin{aligned} V_{DSS} &= 1000V \\ I_{D25} &= 65A \\ R_{DS(on)} &\leq 89m\Omega \end{aligned}$$

miniBLOC, SOT-227
E153432



G = Gate
S = Source
D = Drain

Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ\text{C}$ to 150°C	1000	V
V_{DGR}	$T_J = 25^\circ\text{C}$ to 150°C , $R_{GS} = 1M\Omega$	1000	V
V_{GSS}	Continuous	± 30	V
V_{GSM}	Transient	± 40	V
I_{D25}	$T_C = 25^\circ\text{C}$	65	A
I_{DM}	$T_C = 25^\circ\text{C}$, Pulse Width Limited by T_{JM}	150	A
I_A	$T_C = 25^\circ\text{C}$	25	A
E_{AS}	$T_C = 25^\circ\text{C}$	2.5	J
P_D	$T_C = 25^\circ\text{C}$	1200	W
dv/dt	$I_S \leq I_{DM}$, $V_{DD} \leq V_{DSS}$, $T_J \leq 150^\circ\text{C}$	50	V/ns
T_J		-55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
V_{ISOL}	50/60 Hz, RMS $I_{ISOL} \leq 1\text{mA}$	$t = 1$ minute $t = 1$ second	2500 V~ 3000 V~
M_d	Mounting Torque Terminal Connection Torque	1.5/13 1.3/11.5	Nm/lb.in Nm/lb.in
Weight		30	g

Symbol	Test Conditions	Characteristic Values		
	$(T_J = 25^\circ\text{C}$ Unless Otherwise Specified)	Min.	Typ.	Max.
BV_{DSS}	$V_{GS} = 0V$, $I_D = 1\text{mA}$	1000		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 8\text{mA}$	3.5		6.0 V
I_{GSS}	$V_{GS} = \pm 30V$, $V_{DS} = 0V$			± 200 nA
I_{DSS}	$V_{DS} = V_{DSS}$, $V_{GS} = 0V$ $T_J = 125^\circ\text{C}$			50 μA 7.5 mA
$R_{DS(on)}$	$V_{GS} = 10V$, $I_D = 35A$, Note 1			89 m Ω

Features

- International Standard Package
- miniBLOC, with Aluminium Nitride Isolation
- Isolation Voltage 2500V~
- High Current Handling Capability
- Avalanche Rated
- Low $R_{DS(on)}$

Advantages

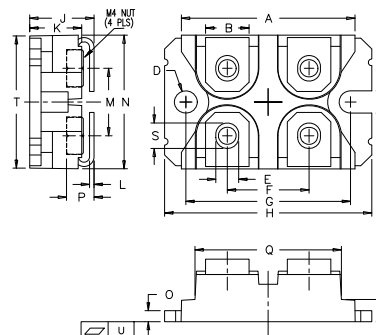
- High Power Density
- Easy to Mount
- Space Savings

Applications

- Switch-Mode and Resonant-Mode Power Supplies
- DC-DC Converters
- PFC Circuits
- AC and DC Motor Drives
- Robotics and Servo Controls

Symbol	Test Conditions (T _J = 25°C, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max
g_{fs}	V _{DS} = 20V, I _D = 35A, Note 1	34	57	S
R_{Gi}	Gate Input Resistance		0.30	Ω
C_{iss}	V _{GS} = 0V, V _{DS} = 25V, f = 1MHz		9150	pF
C_{oss}			2650	pF
C_{rss}			72	pF
Effective Output Capacitance				
C_{o(er)}	Energy related	V _{GS} = 0V V _{DS} = 0.8 • V _{DSS}	390	pF
C_{o(tr)}	Time related		1500	pF
t_{d(on)}	Resistive Switching Times V _{GS} = 10V, V _{DS} = 0.5 • V _{DSS} , I _D = 35A R _G = 1Ω (External)		48	ns
t_r			20	ns
t_{d(off)}			127	ns
t_f			9	ns
Q_{g(on)}	V _{GS} = 10V, V _{DS} = 0.5 • V _{DSS} , I _D = 35A		350	nC
Q_{gs}			84	nC
Q_{gd}			190	nC
R_{thJC}				0.104 °C/W
R_{thCS}			0.05	°C/W

SOT-227B (IXFN) Outline



(M4 screws (4x) supplied)

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	1.240	1.255	31.50	31.88
B	.307	.323	7.80	8.20
C	.161	.169	4.09	4.29
D	.161	.169	4.09	4.29
E	.161	.169	4.09	4.29
F	.587	.595	14.91	15.11
G	1.186	1.193	30.12	30.30
H	1.496	1.505	38.00	38.23
J	.460	.481	11.68	12.22
K	.351	.378	8.92	9.60
L	.030	.033	0.76	0.84
M	.496	.506	12.60	12.85
N	.990	1.001	25.15	25.42
O	.078	.084	1.98	2.13
P	.195	.235	4.95	5.97
Q	1.045	1.059	26.54	26.90
R	.155	.174	3.94	4.42
S	.186	.191	4.72	4.85
T	.968	.987	24.59	25.07
U	-.002	.004	-0.05	0.1

Source-Drain Diode

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
I_S	$V_{GS} = 0\text{V}$			70 A
I_{SM}	Repetitive, Pulse Width Limited by T_{JM}			280 A
V_{SD}	$I_F = I_S$, $V_{GS} = 0\text{V}$, Note 1			1.4 V
t_{rr}	$I_F = 35\text{A}$, $-di/dt = 100\text{A}/\mu\text{s}$ $V_R = 100\text{V}$, $V_{GS} = 0\text{V}$		310	ns
Q_{RM}			3.5	μC
I_{RM}			22.6	A

Note 1. Pulse test, $t \leq 300\mu\text{s}$, duty cycle, $d \leq 2\%$.

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
4,860,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

Fig. 1. Output Characteristics @ $T_J = 25^\circ\text{C}$

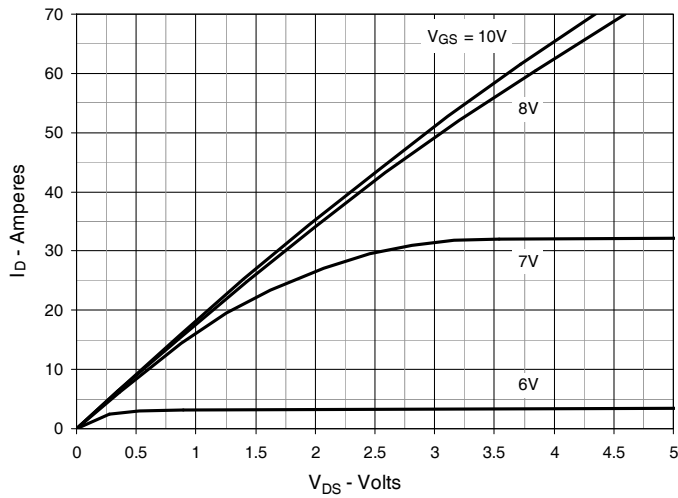


Fig. 2. Extended Output Characteristics @ $T_J = 25^\circ\text{C}$

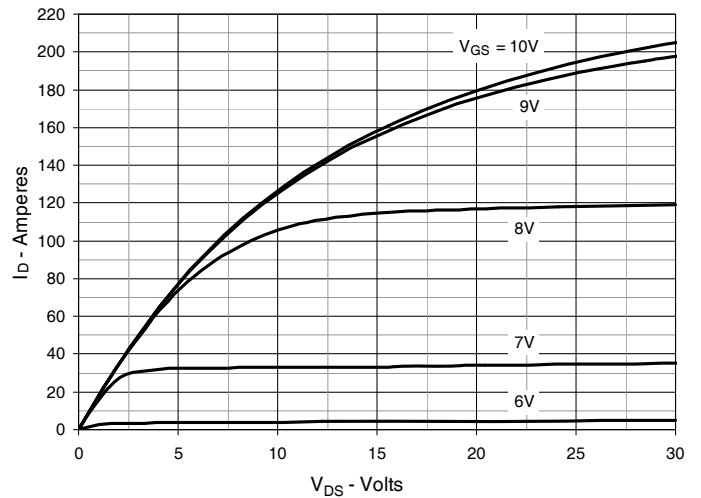


Fig. 3. Output Characteristics @ $T_J = 125^\circ\text{C}$

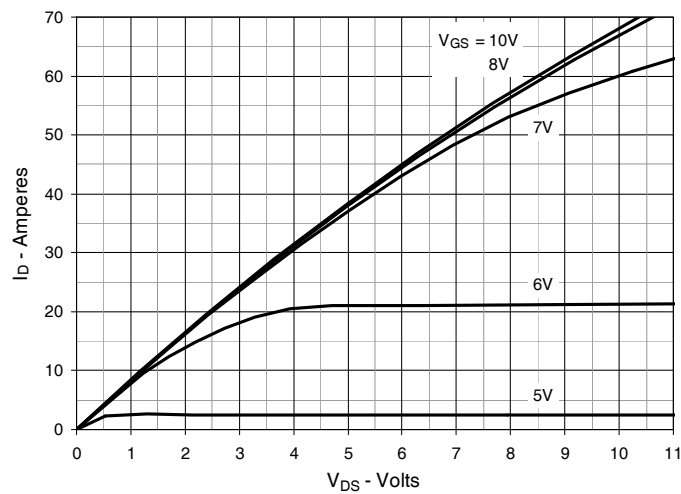


Fig. 4. $R_{DS(on)}$ Normalized to $I_D = 35\text{A}$ Value vs. Junction Temperature

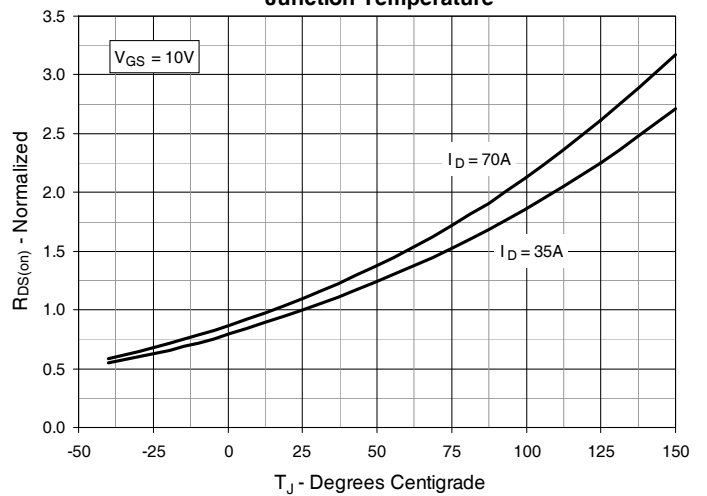


Fig. 5. $R_{DS(on)}$ Normalized to $I_D = 35\text{A}$ Value vs. Drain Current

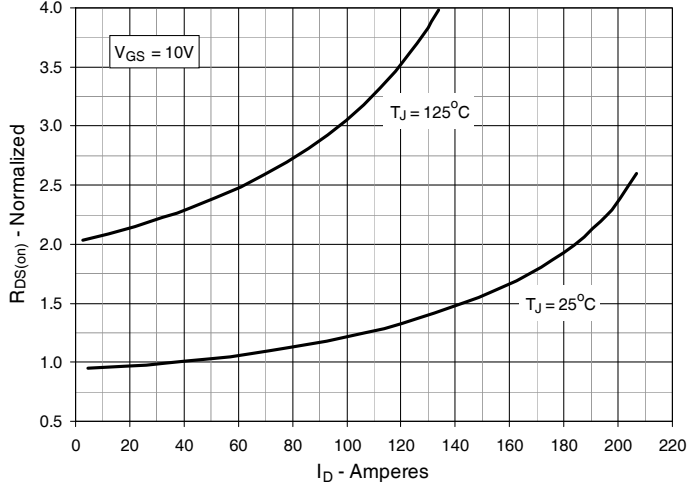


Fig. 6. Normalized Breakdown & Threshold Voltages vs. Junction Temperature

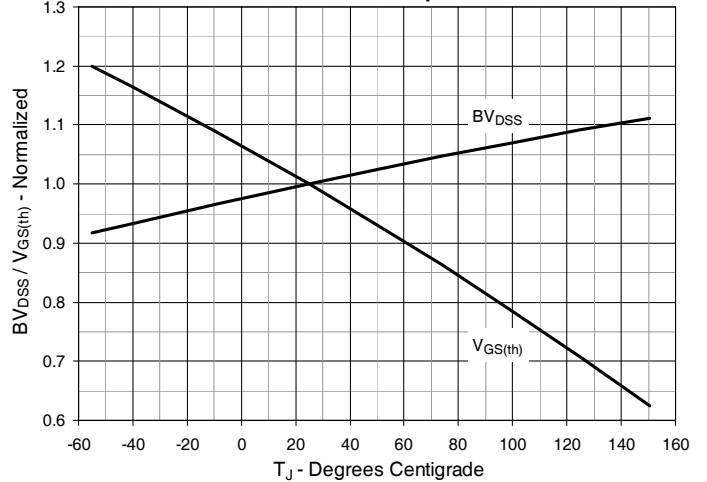


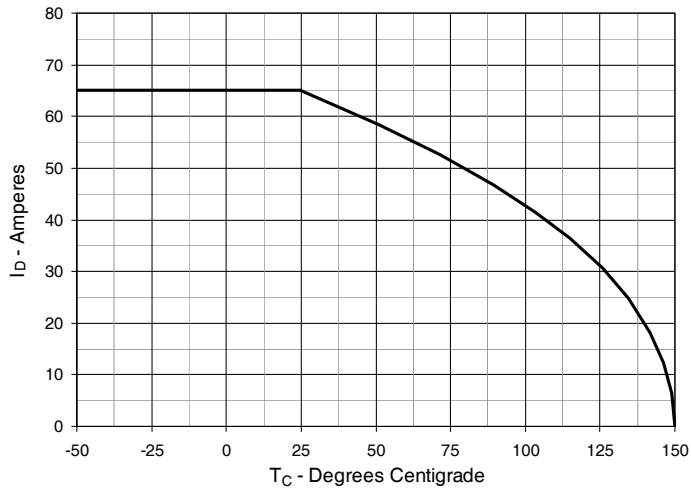
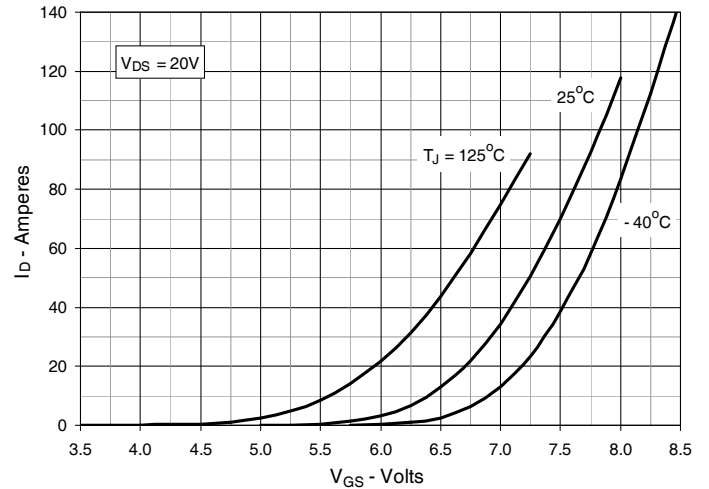
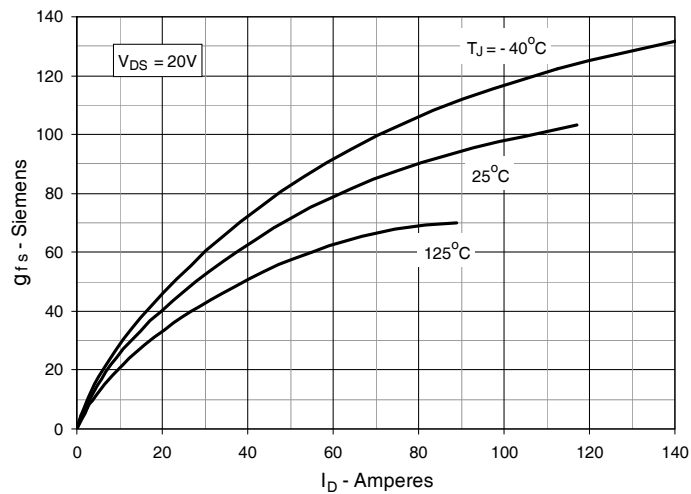
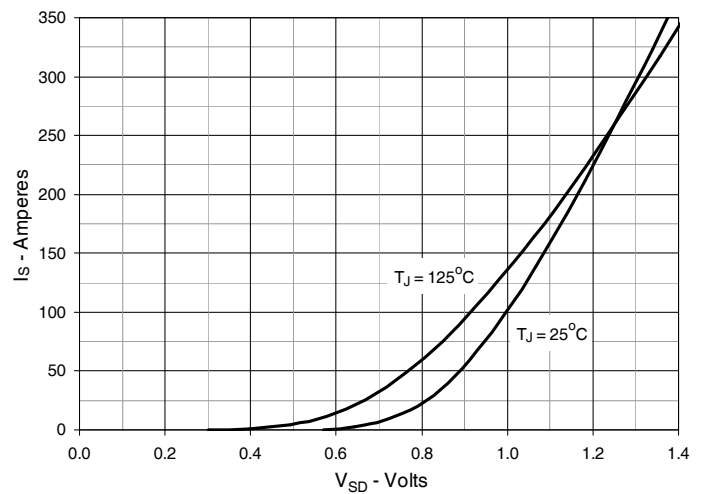
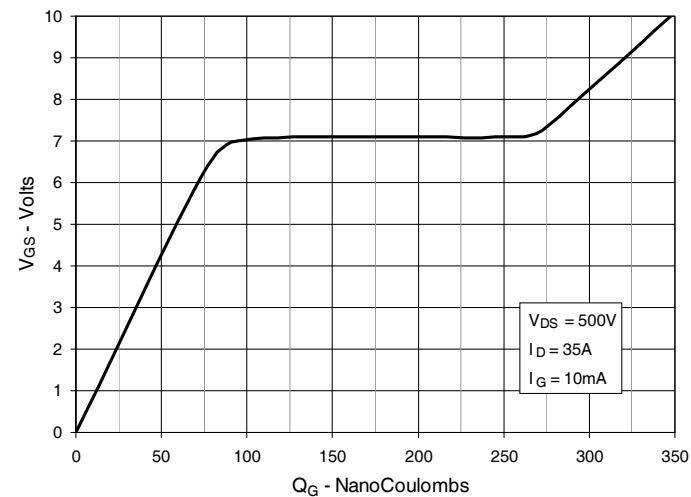
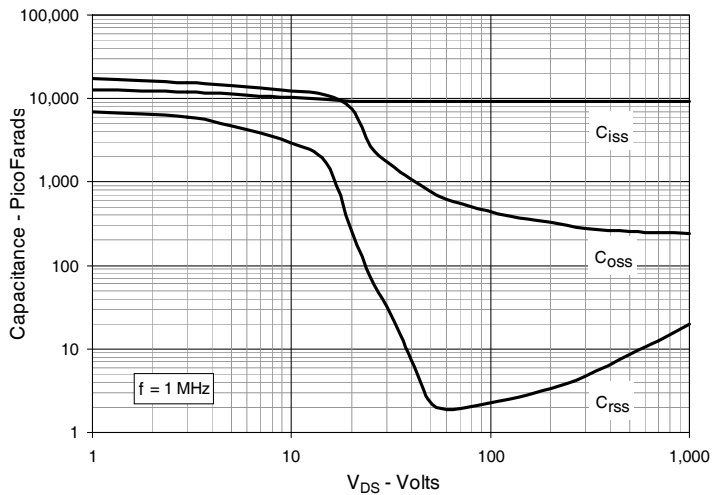
Fig. 7. Maximum Drain Current vs. Case Temperature

Fig. 8. Input Admittance

Fig. 9. Transconductance

Fig. 10. Forward Voltage Drop of Intrinsic Diode

Fig. 11. Gate Charge

Fig. 12. Capacitance


Fig. 13. Output Capacitance Stored Energy

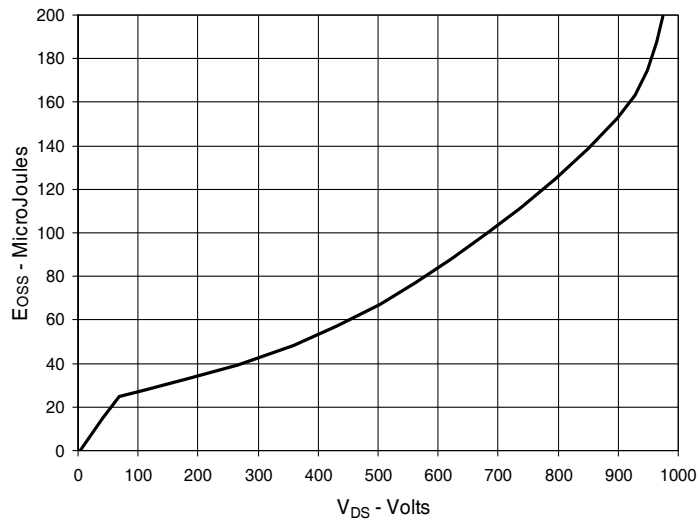


Fig. 14. Forward-Bias Safe Operating Area

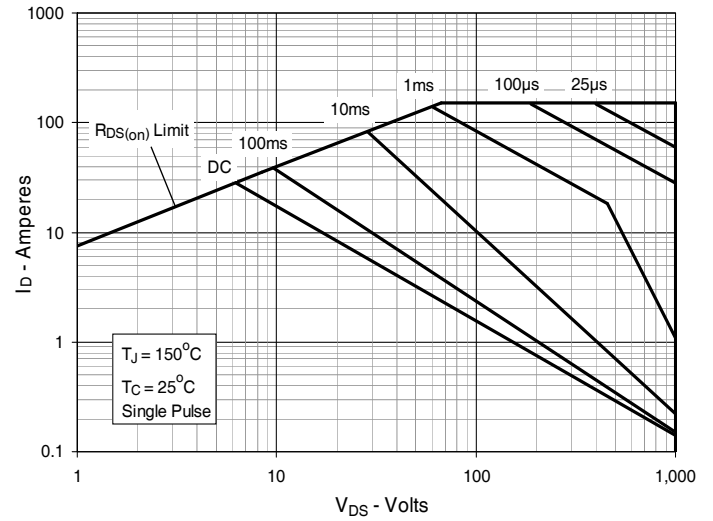


Fig. 15. Maximum Transient Thermal Impedance

